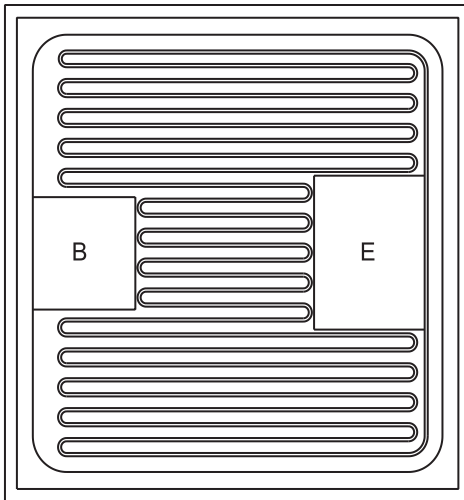


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	41.3 x 41.3 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	9.5 x 9.2 MILS
Emitter Bonding Pad Area	12.8 x 10.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

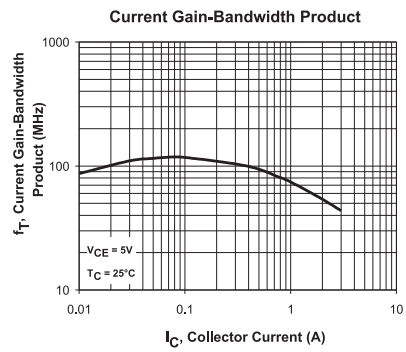
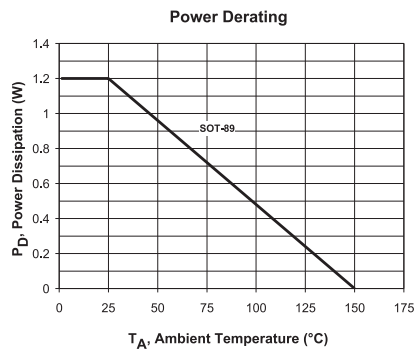
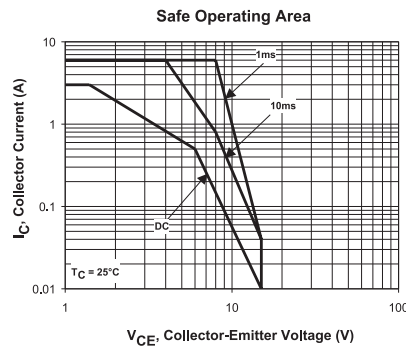
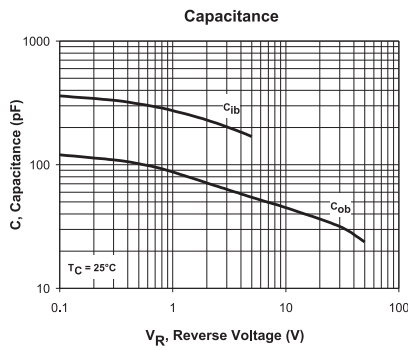
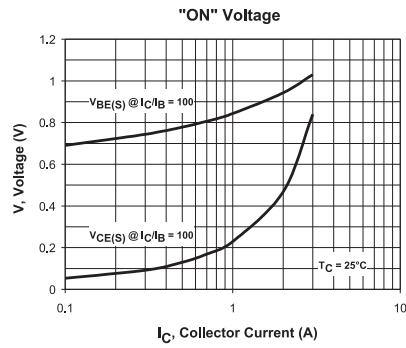
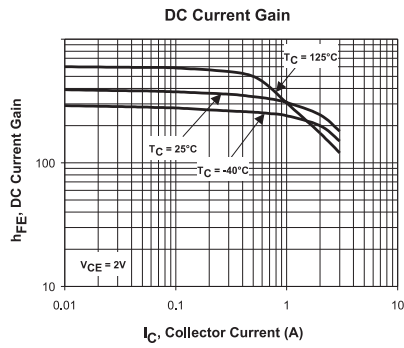
6,670

PRINCIPAL DEVICE TYPES

- CMPT3090L
- CXT3090L
- CZT3090L
- CMXT3090L

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centalsemi.com

R2 (15- September 2003)



145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R2 (15- September 2003)